

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
M1221657SERIAL NO.
Unknown

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Cem. Basceri et al.FILING DATE
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UnknownU.S. PTO
09/905320

07/13/01

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
EE	AA			Cem. Basceri et al. as filed			Filed Concurrently
EE	AB	09 476 516		Cem. Basceri as filed and as amended.			01/03/00
EE	AC	09 580 733		Cem. Basceri as filed.			05/26/00
EE	AD	5 459 635	10/17/95	Tomozawa et al.	361	321.5	
EE	AE	5 618 761	04/08/97	Eguchi et al.	438	785	
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FOREIGN PATENT DOCUMENTS

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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Form PTO 1520

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.
M122-1657

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LIST OF ART CITED BY APPLICANT

Use several sheets if necessary.

APPLICANT
Cem. Basseri et al.

FILING DATE
July 13, 2000

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U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
E	AA	5,256,453	10/26/93	Numasawa			
E	AB	5,731,048	01/21/97	Endo			
E	AC	5,776,254	03/24/98	Yializis et al.			
E	AD	5,783,253	07/07/98	Yuuka et al.			
E	AE	5,798,903	07/21/98	Roh			
E	AF	6,043,526	08/25/98	Diotre et al.			
E	AG	6,046,345	03/28/00	Ochian			
E	AH	6,078,492	04/04/00	Kadokura et al.			
E	AI	6,153,595	06/20/00	Huang et al.			
E	AJ	6,037,205	11/28/00	Watanabe			
E	AK	6,037,205	03/14/00	Huh et al.			

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
E	AL	0,855,715 A2	26/01/98	EPO - Zhao et al., Applied Materials, Inc.				
E	AM	0,957,522 A2	12/05/99	EPO - Ueda, Michihiro, Matsushita Electric Ind. Co.,				
E	AN	WO 98/04997	20/02/98	WIPO - Simpson, John et al.				
E	AO	0,474,140 A1	30/08/91	EPO - Kamayama, Satoshi c/o NEC Corporation				
E	AP	WO 99/64645	11/06/99	WIPO - Narwankar et al., Applied Materials, Inc.				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

E	AR		Steve Bilodeau et al., <i>Composition Dependence of the Dielectric Properties of MOCVD Ba-Sr-TiO₂</i> , pp. 1-21 (MES Fall Meeting 12/01/94)					
E	AS		Steve M. Bilodeau et al., <i>MOCVD BST for High Density DRAM Applications</i> (Preprint for SEMICON/WEST 07/12/95), 2 pages					
E	AT		Y C Chen et al., Abstract, <i>Improvements of the Properties of Chemical Vapor-Deposited (Ba,Sr)-TiO₂ Films Through Use of a Seed Layer</i> , 16 JPN. J. APPL. PHYS. Pt. 1, No. 11, pp. 6824-6828 (1997)					

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Form PTO/BP U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1657		SERIAL NO. 09/905320			
LIST OF ART CITED BY APPLICANT <small>Use several sheets if necessary.</small>				APPLICANT Gen. Bascor et al.			
FILING DATE July 13, 2001				GROUP I, Class. 36			
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
EF	AA	5,470,398	11/28/95	Shibuya et al.			
EF	AI	5,254,805	10/19/93	Kanayama			
EF	AG	6,156,638	12/05/00	Agarwal et al.			
EF	AI	6,165,834	12/26/00	Agarwal et al.			
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LIST OF ART CITED BY APPLICANT <small>Use several sheets if necessary.</small>		APPLICANT Cem Basseri et al.	
FILING DATE July 13, 2001		GROUP Unknown	


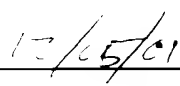
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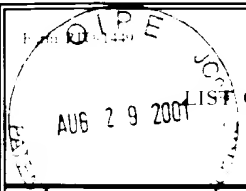

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	AN							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
EF	AR		Takaaki Kawahara et al., <i>(Ba, Sr)TiO₃ Films Prepared by Liquid Source Chemical Vapor Deposition on Ru Electrodes</i> , 35 JPN. J.
			A111. PHYS. Pt. 1, No. 9B, pp. 4880, 4883 (1996).
EF	AS		Rajesh Khamankar et al., <i>A Novel Low-Temperature Process for High Dielectric Constant BST Thin Films for ULSI DRAM</i>
			<i>Applications</i> , Microelectronics Research Center, Univ. of Texas at Austin, TX (Undated), 2 pages.
EF	AT		Yong Tae Kim et al., Abstract, <i>Advantages of RuO₄ bottom electrode in the dielectric and leakage characteristics of</i>
			<i>(Ba, Sr)TiO₃ capacitor</i> , 35 JPN. J. A111. PHYS. Pt. 1, No. 12A, pp. 6153-6156 (1996).

EXAMINER:	DATE CONSIDERED: 12/05/01
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Form PTO-144 <div style="border: 1px solid black; border-radius: 50%; padding: 10px; display: inline-block; text-align: center;"> 012 AUG 29 2001 </div>		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122 1657		SERIAL NO. 09 905 320	
LIST OF ART CITED BY APPLICANT Use several sheets if necessary				APPLICANT Cem. Basceny et al.			
FILING DATE July 13, 2001				GROUP Unknown			
U.S. PATENT DOCUMENTS							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
EF	AR		SH. Paek et al., Abstract, <i>Characterization of MIS capacitor of BST thin films deposited on Si by RF magnetron sputtering</i> .				
			Ferroelectric Thin Films V Symposium, San Francisco, CA, pp. 33-38 (April 7, 1995)				
EF	AS		N. Takeuchi et al., Abstract, <i>Effect of firing atmosphere on the cubic-hexagonal transition in Ba_{0.8}Sr_{0.2}TiO₃</i> , 98 JAPANESE				
			KERAMIKUSI KYOKAI GAKUJI SHI RONBUNSHI No. 8, pp. 836-839 (1990)				
EF	AT		H. Yamaguchi, et al., Abstract, <i>Reactive coevaporation synthesis and characterization of SrTiO₃, BaTiO₃ thin films</i> , IEEE				
			International Symposium on Applications of Ferroelectrics, Greenville, SC, pp. 285-288 (August 2, 1992)				
EXAMINER			DATE CONSIDERED				
							
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		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22 1677		SERIAL NO. 09 065 320		
		LIST OF ART CITED BY APPLICANT <small>Use several sheets if necessary</small>						
		APPLICANT Gen. Basciet et al.		FILING DATE July 13, 2001		GROUP A (see art.)		
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
EF	AR		S. Yamamuchi et al., Abstract, <i>Ba + Sr/Ti ratio dependence of the dielectric properties for (Ba_{1-x}Sr_xTiO₃) thin films prepared by ion beam sputtering</i> , 64 APPLIED PHYSICS LETTERS No. 13, pp. 1644-1646 (1994).					
			35 JPS J. of Appl. Phys. Pt. 1, No. 2A, pp. 729-735 (1996).					
EF	AS		M. Yamamuka et al., Abstract, <i>Thermal-Desorption Spectroscopy of (Ba,Sr,TiO₃) Thin-Films Prepared by Chemical-Vapor-Deposition</i> .					
			35 JPS J. of Appl. Phys. Pt. 1, No. 2A, pp. 729-735 (1996).					
EF	AT		Arai I., et al., <i>Preparation of SrTiO₃ Films on 8-Inch Wafers by Chemical Vapor Deposition</i> , Jap. Journal of Applied Physics, Vol. 35,					
			No. 9B, Part 01, 09 01 96, Pgs. 4875-4879.					
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LIST OF ART CITED BY APPLICANT <small>(Use several sheets if necessary.)</small>				APPLICANT Cem. Bascen et al.		GROUP Unknown	
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CF	AR		Kim, et al. <i>Structural and Electrical Properties of BaTiO₃ grown on p-InP (100) by low-pressure metalorganic chemical vapor deposition at low temperature</i> , Applied Physics Letters, U.S. American Institute of Physics Vol. 65, No. 15, 10/10/94, Pgs. 1955-1957				
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